

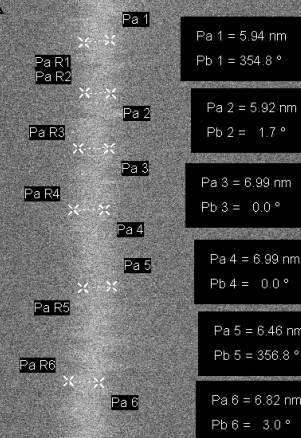
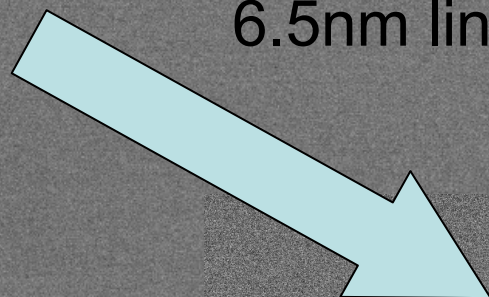
JEOL JBX-9300FS Electron Beam Lithography System

Enabling Nanotechnology

Georgia Tech Microelectronics Research Center

Ebeam Resist: Hydrogen Silsesquioxane (HSQ)
Resist Type: Negative
Resist Thickness: 19nm
Developer: 2.3% TMAH
Beam energy: 100kV
Beam current: 100pA
Electron dose: 33,600 $\mu\text{C}/\text{cm}^2$
Substrate: Silicon
pattern: isolated single pixel width line

6.5nm line



Mag = 10.00 K X 

EHT = 2.00 kV
WD = 2 mm

Signal
Photo

Mag = 968.00 K X 

EHT = 2.00 kV
WD = 2 mm

Signal A = SE2
Photo No. = 3062

Date :15 Feb 2005
Time :9:39:40